

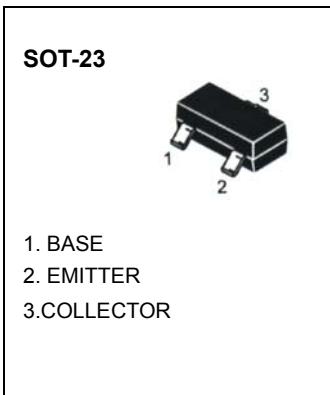
TRANSISTOR (NPN)

FEATURES

- High emitter-base voltage
- low on resistance

MARKING: MAX

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)



Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	12	V
I_c	Collector Current -Continuous	0.3	A
P_c	Collector Power Dissipation	0.2	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	12			V
Collector cut-off current	I_{CBO}	$V_{CB}=25\text{ V}, I_E=0$			0.1	$\mu\text{ A}$
Emitter cut-off current	I_{EBO}	$V_{EB}=12\text{V}, I_C=0$			0.1	$\mu\text{ A}$
DC current gain	$h_{FE}(\text{FOR})$	$V_{CE}=2\text{V}, I_C=4\text{ mA}$	200		1000	
	$h_{FE}(\text{REV})$	$V_{CE}=2\text{V}, I_C=4\text{mA}$	20			
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C=100\text{mA}, I_B=10\text{ mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=1\text{mA}$ $f=100\text{MHz}$		60		MHz
output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		10		pF
On resistance	$R_{(\text{on})}$	$V_{in}=0.3\text{V}, I_B=1\text{mA}, f=1\text{KHz}$		0.6		Ω

Typical characteristics

